

1SS357

SILICON EPITAXIAL SCHOTTKY BARRIER DIODE

Features

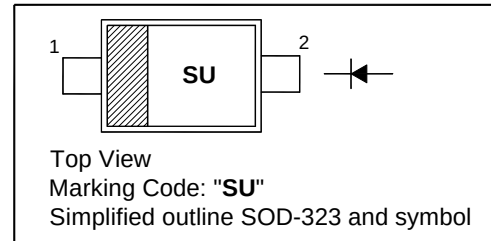
- Low forward voltage
- Low reverse current

Applications

- High Speed Switching

PINNING

PIN	DESCRIPTION
1	Cathode
2	Anode



Absolute Maximum Ratings ($T_a = 25\text{ }^{\circ}\text{C}$)

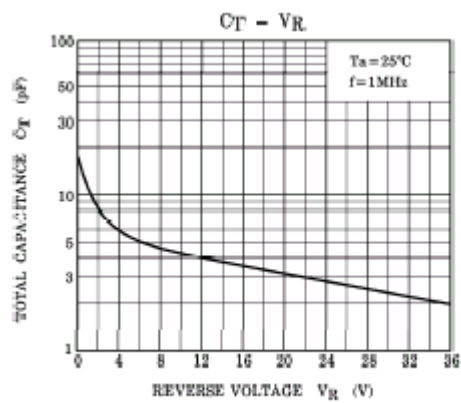
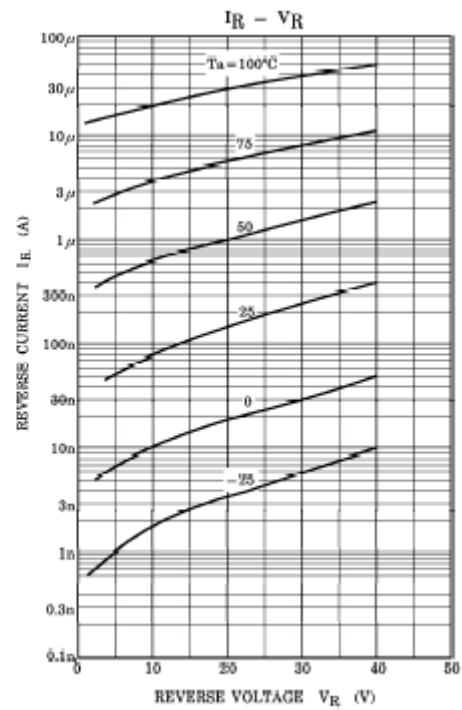
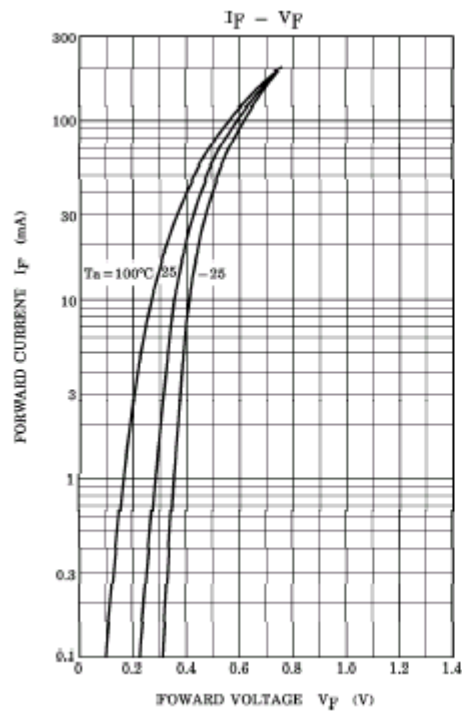
Parameter	Symbol	Value	Unit
Maximum (Peak) Reverse Voltage	V_{RM}	45	V
Reverse Voltage	V_R	40	V
Average Forward Current	$I_{F(AV)}$	100	mA
Maximum (Peak) Forward Current	I_{FM}	300	mA
Surge Forward Current (10 ms)	I_{FSM}	1	A
Power Dissipation	P_{tot}	200	mW
Junction Temperature	T_j	125	$^{\circ}\text{C}$
Storage Temperature Range	T_{stg}	- 55 to + 125	$^{\circ}\text{C}$

Characteristics at $T_a = 25\text{ }^{\circ}\text{C}$

Parameter	Symbol	Max.	Unit
Forward Voltage at $I_F = 100\text{ mA}$	V_F	0.6	V
Reverse Current at $V_R = 40\text{ V}$	I_R	5	μA
Total Capacitance at $V_R = 0, f = 1\text{ MHz}$	C_T	25	pF



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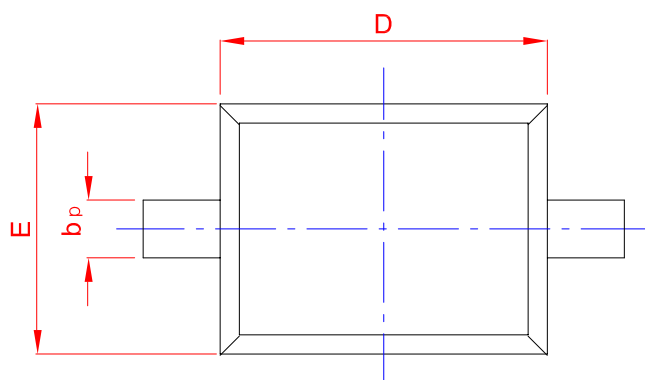
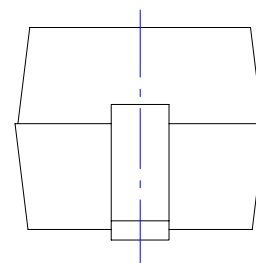
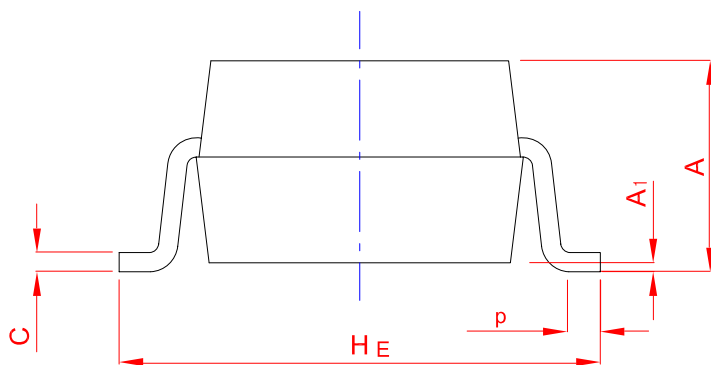
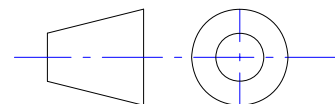


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PACKAGE OUTLINE

Plastic surface mounted package; 2 leads

SOD-323



UNIT	A	bp	C	D	E	HE	A1	Lp
mm	1.20 0.90	0.40 0.25	0.15 0.10	1.80 1.60	1.35 1.15	2.80 2.30	0.10 0.01	0.50 0.20